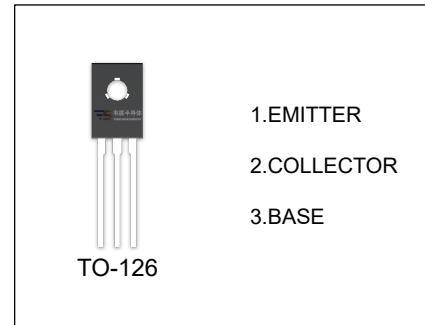


KSD1691 TRANSISTOR (NPN)

FEATURES

- Low Collector-Emitter Saturation Voltage & Large Collector Current
- High Power Dissipation: $P_C = 1.3W$ ($T_a=25^\circ C$)



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
KSD1691	TO-126	Bulk	200pcs/Bag
KSD1691-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	5	A
P_C	Collector Power Dissipation ($T_a = 25^\circ C$)	1.3	W
	Collector Power Dissipation ($T_c = 25^\circ C$)	20	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^\circ C$

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}, I_E=0$			10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=2\text{A}$	100		400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=0.1\text{A}$	60			
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=5\text{A}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{A}, I_B=0.2\text{A}$			1.2	V
Turn ON Time	t_{on}	$V_{CC} = 10\text{V}, I_C = 2\text{A}, I_{B1}=-I_{B2}=0.2\text{A}, R_L=5\Omega$			1	μS
Storage Time	t_{stg}				2.5	μS
Fall Time	t_f				1	μS

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	G
Range	100-200	160-320	200-400